## imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



### Contact us

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# **PHOTONIC**Silicon Photodiode, Filter Combination Photovoltaic**DETECTORS INC.**(center wavelength 436 nm) Type PDB-V443.6



PACKAGE DIMENSIONS INCH [mm] EPOXY MARKING INK (WAVE LENGTH NO.) ACTIVE AREA SURFACE 0.365 [9.27] 0.355 [9.02] EPOXY COVERING + 0.005 [0.13] - 0.080 [2.03] 0.345 [8.76] 0.200 [5.08] DIA PIN CIRCLE 0.335 [8.51] 0.245 [6.22] 0.235 [5.97] DIA .500 [12.70] 늡 45 ANODE 0.020 [0.51] DIA 2 PLACES CATHODE (CASE GROUND) WIRE BONDS 0.330 [8.38] 0.320 [8.13] DIA 0.035 [0.89] FILTER CAP SUBASSEMBL 0.425 [10.80] ACTIVE AREA 0.223 [5.66] 0.123 [3.12] 0.135 [3.43] ACTIVE AREA **TO-5 CAN PACKAGE** 0.235 [5.97] ACTIVE AREA =  $17.74 \text{ mm}^2$ 

RESPONSIVITY (AW)

#### **FEATURES**

- 436 +/- 2 nm CWL
- 10 nm FWHM
- 45% transmission
- 10<sup>-4</sup> rejection

#### DESCRIPTION

The **PDB-V443.6** is a silicon, PIN planar diffused, photodiode with a narrow band interference filter. The detector filter combination has a narrow 10 nm balf bandwidth designed, for low paise photovoltain

half bandwidth designed for low noise photovoltaic applications. Packaged in a TO-5 metal can.

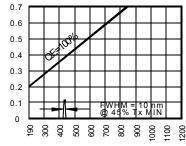
#### **APPLICATIONS**

- Spectrophotometry
- Chemistry instrumentation
- Liquid chromatography

#### **ABSOLUTE MAXIMUM RATING** (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
Vbr	Reverse Voltage		100	V	
T <sub>STG</sub>	Storage Temperature	-20	+85	оС	
To	Operating Temperature Range	-15	+70	°C	
Ts	Soldering Temperature*		+240	°C	
Ι	Light Current		500	mA	





WAVELENGTH(nm)

\*1/16 inch from case for 3 secs max

#### **ELECTRO-OPTICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μΑ
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 mV		10	50	pА
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	.20	2		GΩ
TC RSH	RsH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C
CJ	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		1700		pF
CWL	Center Wavelength	(CWL, $\lambda$ o) +/- 2 nm		436		nm
HBW	Half Bandwidth	(FWHM)		10		nm
Vbr	Breakdown Voltage	I = 10 μA	50	75		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 mV @ Peak		9x10 <sup>-15</sup>		W/ √ Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 10 V		1.0		μS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f=1 MHz, \*\*\* without filter [FORM NO. 100-PDB-V443.6 REV N/C]